

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	270	(@ad<="20021118") and (216/56.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/15 10:40
L2	29	(@ad<="20021118") and (216/56.ccls.) and nano\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/15 10:45
L3	12	(@ad<="20021118") and ("216"/\$3.ccls.) and nanowires	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/15 10:51
L4	28	(@ad<="20021118") and ("205"/\$3.ccls.) and nanowires	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/15 10:51
S1	2059	nanowires	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 06:55
S2	1272	nanowires and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 13:00
S3	245	nanowires and semiconductor and dispersion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 13:00
S4	87	(@ad<="20021118") and nanowires and semiconductor and dispersion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 13:36
S5	53	(@ad<="20021118") and nanowires and semiconductor and dispersion and etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 13:02
S6	28	(@ad<="20021118") and nanowires and semiconductor and dispersion and etch\$4 and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 10:13

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S7	28	(@ad<="20021118") and nanowires and semiconductor and dispersion and etch\$4 and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 17:01
S8	0	(@ad<="20021118") and (manufacturing adj nanowires) and semiconductor and dispersion and etch\$4 and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 13:16
S9	0	(@ad<="20021118") and (manufactur\$4 with nanowires) and semiconductor and dispersion and etch\$4 and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 13:16
S10	145	(@ad<="20021118") and nanowires and semiconductor and etch\$4 and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 15:13
S11	75	(@ad<="20021118") and nanowires and semiconductor and etch\$4 and mask and anod\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 17:42
S12	16	(@ad<="20021118") and nanowires and semiconductor and etch\$4 and mask and anodically	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 17:42
S13	3	(@ad<="20021118") and nanowires and semiconductor and etch\$4 and mask and (anodically with etch\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/06 12:48
S14	35	(@ad<="20021118") and nanowires and semiconductor and etch\$4 and mask and ((anodically or electrochemical\$4) with etch\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 18:20
S15	117	(@ad<="20021118") and (nanowire or nanotube or nanostructure) and semiconductor and etch\$4 and mask and ((anodically or electrochemical\$4) with etch\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 18:21
S16	14	("2001/0054709").URPN.	USPAT	OR	ON	2006/03/28 18:31
S17	14	("2001/0054709").URPN.	USPAT	OR	ON	2006/03/28 18:33
S18	14	("2001/0054709").URPN.	USPAT	OR	ON	2006/03/28 18:34

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S19	257	nanowires and oxidation and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 06:55
S20	25	"5607876"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 09:31
S21	14	(@ad<="20021118") and nanowires and semiconductor and dispersion and vibration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 10:58
S22	65	(@ad<="20021118") and nanowires and semiconductor and dispersion and (vibrat\$4 or ultrasonic or ulta or remov\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 11:03
S23	24	(@ad<="20021118") and nanowires and semiconductor and dispersion and (vibrat\$4 or ultrasonic or ulta)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 12:11
S24	27	(@ad<="20021118") and nanowires and sol-gel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:39
S25	0	Van-den-meerakker.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:40
S26	0	(Van-den-meerakker.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:41
S27	0	(blaaderen-alfons.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:41
S28	0	(carlos-maria-van-kats.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:41

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S29	474739	(Van den meerakker.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:42
S30	31	(meerakker.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:42
S31	4	((("5987208") or ("5607876"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/13 18:13
S32	2	("5607876").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/05 16:51
S33	234	(@ad<="20021118") and nanowires and etch\$4 and (holes or pores)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 17:02
S34	1	(@ad<="20021118") and nanowires and substrate and dispersion and coloring	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/06 12:49
S35	95	(@ad<="20021118") and (nanowires with etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 09:48
S36	665	(@ad<="20021118") and (438/691.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/15 10:40
S37	10	(@ad<="20021118") and (438/691.ccls.) and nano	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 10:14
S38	1	(@ad<="20021118") and (438/691.ccls.) and nanowire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 10:15

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S39	137	(@ad<="20021118") and ("438"/\$.ccls.) and nanowire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 10:17
S40	23	(@ad<="20021118") and ("438"/\$.ccls.) and (nanowire same etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 10:24
S41	2	("6359288").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/13 13:12
S42	131	(@ad<="20021118") and (nanowire same etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 10:24
S43	2	("20030098640").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/13 12:09
S44	2	("6221777").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/13 13:12
S45	75	(@ad<="20021118") and nanowires and semiconductor and dispersion and (um or micron or micrometer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/13 15:39
S46	23	(@ad<="20021118") and nanowires and semiconductor and dispersion and ((um or micron or micrometer) with length with nanowire)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 11:52
S47	2	("20040065022").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 11:52
S48	2	("20020176276").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 17:04